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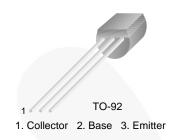
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### BC546 / BC547 / BC548 / BC549 / BC550 NPN Epitaxial Silicon Transistor

#### Features

- Switching and Amplifier
- High-Voltage: BC546, V<sub>CEO</sub> = 65 V
- Low-Noise: BC549, BC550
- Complement to BC556, BC557, BC558, BC559, and BC560



#### **Ordering Information**

Part Number	Marking	Package	Packing Method
BC546ABU	BC546A	TO-92 3L	Bulk
BC546ATA	BC546A	TO-92 3L	Ammo
BC546BTA	BC546B	TO-92 3L	Ammo
BC546BTF	BC546B	TO-92 3L	Tape and Reel
BC546CTA	BC546C	TO-92 3L	Ammo
BC547ATA	BC547A	TO-92 3L	Ammo
BC547B	BC547B	TO-92 3L	Bulk
BC547BBU	BC547B	TO-92 3L	Bulk
BC547BTA	BC547B	TO-92 3L	Ammo
BC547BTF	BC547B	TO-92 3L	Tape and Reel
BC547CBU	BC547C	TO-92 3L	Bulk
BC547CTA	BC547C	TO-92 3L	Ammo
BC547CTFR	BC547C	TO-92 3L	Tape and Reel
BC548BU	BC548	TO-92 3L	Bulk
BC548BTA	BC548B	TO-92 3L	Ammo
BC548CTA	BC548C	TO-92 3L	Ammo
BC549BTA	BC549B	TO-92 3L	Ammo
BC549BTF	BC549B	TO-92 3L	Tape and Reel
BC549CTA	BC549C	TO-92 3L	Ammo
BC550CBU	BC550C	TO-92 3L	Bulk
BC550CTA	BC550C	TO-92 3L	Ammo

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#### **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25^{\circ}$ C unless otherwise noted.

Symbol	Parame	Value	Unit		
V <sub>CBO</sub>		BC546	80		
	Collector-Base Voltage	BC547 / BC550	50	V	
		BC548 / BC549	30		
		BC546	65		
V <sub>CEO</sub>	Collector-Emitter Voltage	BC547 / BC550	45	V	
		BC548 / BC549	30		
V	Emitter-Base Voltage	BC546 / BC547	6	V	
V <sub>EBO</sub> E		BC548 / BC549 / BC550	5	v	
Ι <sub>C</sub>	Collector Current (DC)		100	mA	
P <sub>C</sub>	Collector Power Dissipation		500	mW	
TJ	Junction Temperature		150	°C	
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C	

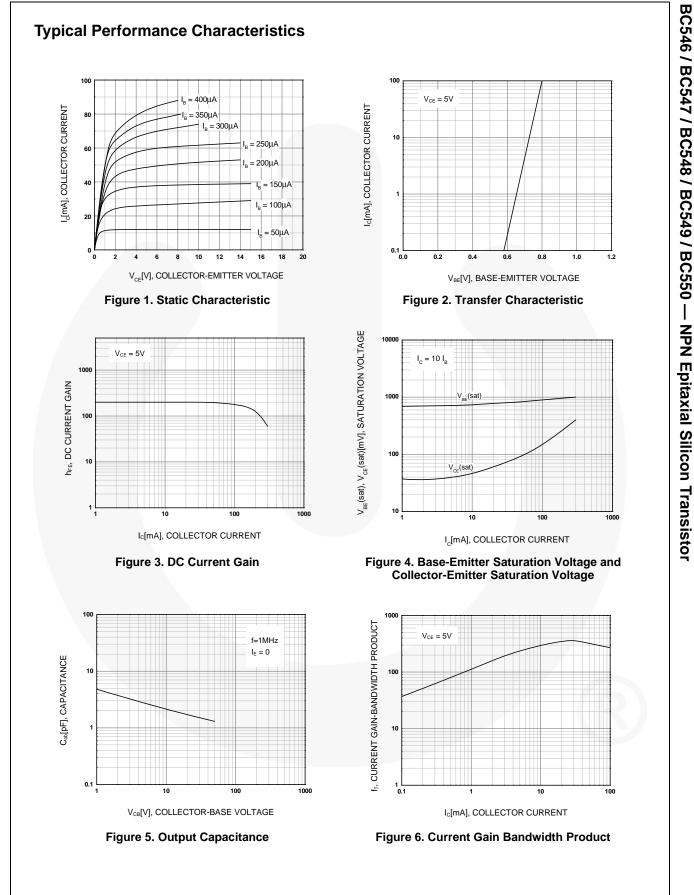
#### **Electrical Characteristics**

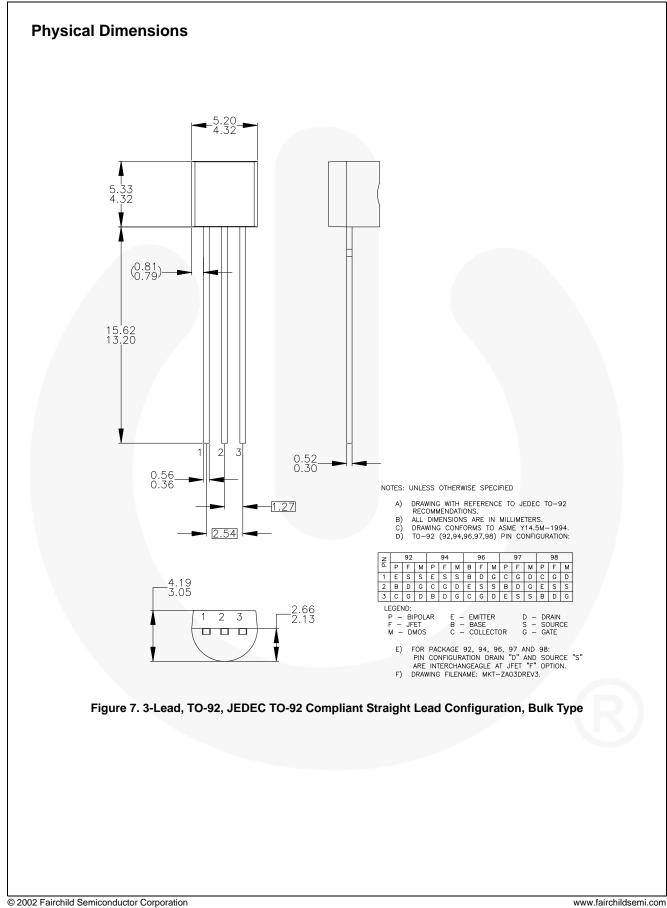
Values are at  $T_A = 25^{\circ}C$  unless otherwise noted.

Symbol		Parameter	Conditions	Min.	Тур.	Max.	Unit
I <sub>CBO</sub>	Collector Cut-Off Current		$V_{CB} = 30 \text{ V}, I_{E} = 0$			15	nA
h <sub>FE</sub>	DC Current Gain		$V_{CE} = 5 \text{ V}, \text{ I}_{C} = 2 \text{ mA}$	110		800	
Vor(sat)	Collector	r-Emitter Saturation	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0.5$ mA		90	250	mV
	Voltage		$I_{\rm C} = 100 \text{ mA}, I_{\rm B} = 5 \text{ mA}$		250	600	
V <sub>BE</sub> (sat) Base-Er	Booo En	aittor Soturation Voltago	$I_{\rm C} = 10$ mA, $I_{\rm B} = 0.5$ mA		700		mV
	Dase-Ell	nitter Saturation Voltage	I <sub>C</sub> = 100 mA, I <sub>B</sub> = 5 mA		900		
V <sub>BE</sub> (on) Base-Er	aittar On Valtaga	$V_{CE} = 5 \text{ V}, I_{C} = 2 \text{ mA}$	580	660	700		
	Dase-En	nitter On Voltage	$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA}$			720	mV
f <sub>T</sub>	Current Gain Bandwidth Product		$V_{CE} = 5 \text{ V}, I_{C} = 10 \text{ mA},$ f = 100 MHz		300		MHz
C <sub>ob</sub>	Output Capacitance		$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		3.5	6.0	pF
C <sub>ib</sub>	Input Capacitance		V <sub>EB</sub> = 0.5 V, I <sub>C</sub> = 0, f = 1 MHz		9		pF
NE	Noise Figure	BC546 / BC547 / BC548	$\label{eq:VCE} \begin{array}{l} V_{CE} = 5 \ V, \ I_{C} = 200 \ \muA, \\ f = 1 \ kHz, \ R_{G} = 2 \ k\Omega \end{array}$		2.0	10.0	dB
		BC549 / BC550			1.2	4.0	
		BC549	$V_{CE} = 5$ V, I <sub>C</sub> = 200 μA, R <sub>G</sub> = 2 kΩ, f = 30 to 15000 MHz		1.4	4.0	
		BC550			1.4	3.0	

#### h<sub>FE</sub> Classification

Classification	Α	В	C
h <sub>FE</sub>	110 ~ 220	200 ~ 450	420 ~ 800





BC546 / BC547 / BC548 / BC549 / BC550 — NPN Epitaxial Silicon Transistor

